

SILICON TRANSISTOR 2SD2403

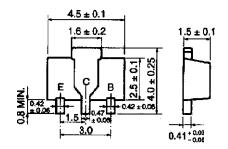
NPN SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS AND MID-SPEED SWITCHING

The 2SD2403 is a transistor featuring high current capacitance in small dimension. This transistor is ideal for DC/DC converters and motor drivers.

FEATURES

- · High current capacitance
- · Low collector saturation voltage
- Complementary transistor with 2SB1572

PACKAGE DRAWING (UNIT: mm)



Electrode Connection

E : Emitter

C : Collector(Fin)
B : Base

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		80	V
Collector to emitter voltage	VCEO		60	٧
Emitter to base voltage	VEBO		6.0	٧
Collector current (DC)	Ic(DC)		3.0	Α
Collector current (pulse)	IC(pulse)	PW ≤ 10 ms duty cycle ≤ 50 %	5.0	Α
Base current (DC)	I _{B(DC)}		0.2	Α
Base current (pulse)	B(pulse)	PW ≤ 10 ms duty cycle ≤ 50 %	0.4	Α
Total power dissipation	Рт	16 cm ² × 0.7 mm ceramic board mounted	2.0	W
Junction temperature	Tj		150	°C
Storage temperature	T _{stg}		-55 to +150	°C

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

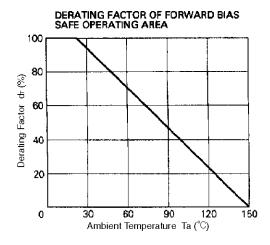
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	VcB = 80 V, IE = 0			100	nA
Emitter cutoff current	ІЕВО	V _{EB} = 6.0 V, I _C = 0			100	nA
DC current gain	h _{FE1}	VcE = 2.0 V, Ic = 0.1 A	80			_
DC current gain	h _{FE2}	Vce = 2.0 V, Ic = 1.0 A	100	200	400	_
DC base voltage	V _{BE}	VcE = 2.0 V, Ic = 0.1 A	630	670	730	mV
Collector saturation voltage	VCE(sat)1	Ic = 2.0 A, Iв = 0.1 A		150	300	mV
Collector saturation voltage	VCE(sat)2	Ic = 3.0 A, I _B = 0.15 A		210	500	mV
Base saturation voltage	V _{BE(sat)}	Ic = 2.0 A, I _B = 0.1 A		0.89	1.2	V
Gain bandwidth product	f⊤	Vce = 10 V, Ie = -0.3 A		130		MHz
Output capacitance	Cob	VcB = 10 V, IE = 0, f = 1 MHz		30		pF
Turn-on time	ton	Ic = 1.0 A, Vcc= 10 V		150		ns
Storage time	tstg	l _{B1} = -l _{B2} = 0.1 A R _L = 5.0 Ω		652		ns
Fall time	tf	nL = 5.0 ½		40		ns

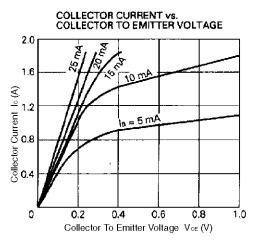
hfe CLASSIFICATION

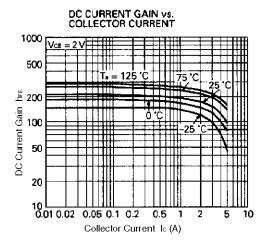
Marking	GX	GY	GZ
h _{FE2}	100 to 200	160 to 320	200 to 400

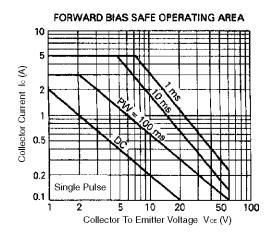


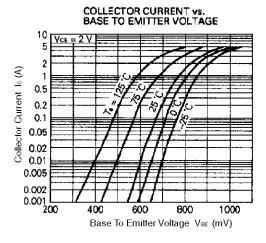
TYPICAL CHARACTERISTICS (Ta = 25°C)

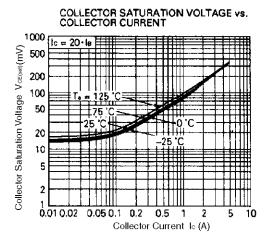






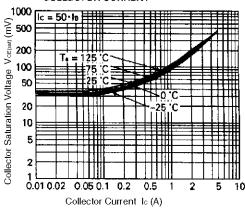




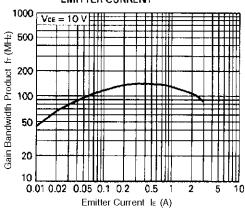


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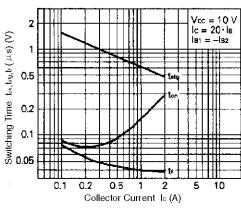




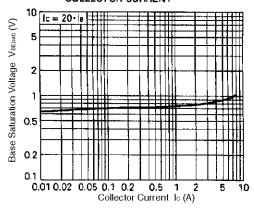
GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



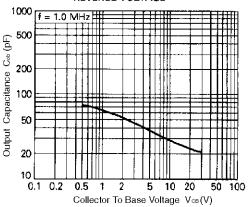
SWITCHING CHARACTERISTICS



BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



OUTPUT CAPACITANCE vs. REVERSE VOLTAGE





[MEMO]

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